

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



November 2013

ISL9R860P2, ISL9R860S3ST 8 A, 600 V, STEALTH™ Diode

Features

- Stealth Recovery trr = 28 ns (@ IF = 8 A)
- Max Forward Voltage, VF = 2.4 V (@ TC = 25°C)
- 600 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

Applications

- SMPS FWD
- · Hard Switched PFC Boost Diode
- · UPS Free Wheeling Diode
- Motor Drive FWD
- · Snubber Diode

Description

The ISL9R860P2, ISL9R860S3ST is a STEALTH™ diode optimized for low loss performance in high frequency hard switched applications. The STEALTH™ family exhibits low reverse recovery current (I_{RR}) and exceptionally soft recovery under typical operating conditions. This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low I_{RR} and short ta phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the STEALTH™ diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Package JEDEC TO-220AC-2L JEDEC TO-263AB(D²-PAK) CATHODE (FLANGE) N/C ANODE N/C ANODE

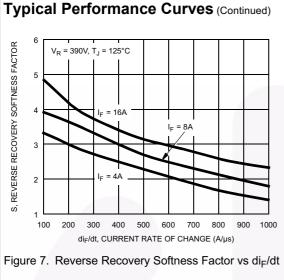
Device Maximum Ratings T_C= 25°C unless otherwise noted

Symbol	Parameter	Ratings	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current (T _C = 147°C)	8	Α
I _{FRM}	Repetitive Peak Surge Current (20kHz Square Wave)	16	Α
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)	100	Α
P _D	Power Dissipation	85	W
E _{AVL}	Avalanche Energy (1 A, 40 mH)	20	mJ
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to 175	°C
T _L T _{PKG}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10s Package Body for 10s, See Techbrief TB334	300 260	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

art Num	ber	Top Mark	Package	Packing Met	hod	Reel Size	Tap	oe Wic	lth C	Quantity	
ISL9R860P2		ISL9R860P2	TO-220AC-2L	Tube		N/A		N/A		50	
SL9R860S3ST ISL9R860S3		ISL9R860S3ST	TO-263AB(D ² -PAK	Reel		13" Dia		24mm		800	
Electric	al (Characteri	Stics T _C = 25°C u	nless otherwise n	oted						
Symbol			Test Conditions			Min	Тур	Max	Unit		
Off State	Ch	aracteristics				<u> </u>					
I _R		Instantaneous Reverse Current		$V_R = 600 \text{ V}$ T_C	To:	= 25°C		-	100	μА	
'R	11130				T _C =	= 125°C		-	1.0	mΑ	
					1.0			1		1	
		aracteristics							•		
V _F	Inst	antaneous Forwa	rd Voltage	I _F = 8 A	T _C =	= 25°C	-	2.0	2.4	V	
					T _C =	= 125°C	-	1.6	2.0	V	
Dynamic	Ch	aracteristics									
СЈ	Jun	ction Capacitance	Э	V _R = 10 V, I _F = 0 A	4		-	30	-	pF	
Switchin	a C	haracteristic	\$					•			
t _{rr}		erse Recovery T		I _F = 1 A, di _F /dt = 1	00 A/u	s. V _D = 30 V	· -	18	25	ns	
	The residence of the second se		$I_F = 8 \text{ A, dig/dt} = 100 \text{ A/µs, V}_R = 30 \text{ V}$			-	21	30	ns		
t _{rr}	Rev	everse Recovery Time		I _F = 8 A, di _F /dt = 200 A/μs, V _R = 390 V, T _C = 25°C			-	28	-	ns	
I _{rr}	Rev	Leverse Recovery Current					-	3.2	-	Α	
Q _{rr}	_	verse Recovery Charge					-	50	-	nC	
t _{rr}	Rev	verse Recovery Time		I _F = 8 A,			-	77	-	ns	
S	Soft	ftness Factor (t _b /t _a)		di _F /dt = 200 A/μs,		-	3.7	-			
I _{rr}	Rev	everse Recovery Current		$V_R = 390 \text{ V},$		Ţ	-	3.4	-	Α	
Q _{rr}	Rev	erse Recovery C	harge	T _C = 125°C		-	150	-	nC		
t _{rr}	Rev	erse Recovery T	ime	I _F = 8 A,			-	53	-	ns	
S	Soft	Softness Factor (t _b /t _a) Reverse Recovery Current Reverse Recovery Charge		di _F /dt = 600 A/µs, V _R = 390 V, T _C = 125°C		-	2.5	-			
Irr	_					-	6.5	-	Α		
Q _{rr}	Rev						195	-	nC		
dI _M /dt	Max	imum di/dt durin	g t _h	l l			-	500	-	A/µs	
\'``.	•									1	
		racteristics								T	
R _{θJC}	+	hermal Resistance Junction to Case					-	-	1.75	°C/W	
R _{θJA}		Thermal Resistance Junction to Ambient					-	-	62	°C/W	
$R_{ hetaJA}$	1 The	rmal Degistance	Junction to Ambient	TO-263					62	°C/W	

Typical Performance Curves 175°C 150°C REVERSE CURRENT (µA) FORWARD CURRENT (A) 12 10 125°C 8 100°C 100°C 6 2 0.5 0.75 1.25 1.5 1.75 V_F, FORWARD VOLTAGE (V) V_R, REVERSE VOLTAGE (V) Figure 1. Forward Current vs Forward Voltage Figure 2. Reverse Current vs Reverse Voltage V_R = 390V, T_J = 125°C V_R = 390V, T_J = 125°C t_b AT $d_F/dt = 200A/\mu s$, 500A/ μs , 800A/ μs 60 t, RECOVERY TIMES (ns) t, RECOVERY TIMES (ns) 60 50 40 30 30 20 10 10 t_a AT $di_F/dt = 200A/\mu s$, $500A/\mu s$, $800A/\mu s$ 300 400 500 600 700 800 900 1000 di_F/dt, CURRENT RATE OF CHANGE (A/µs) 100 I_F, FORWARD CURRENT (A) Figure 4. t_a and t_b Curves vs di_F/dt Figure 3. t_a and t_b Curves vs Forward Current V_R = 390V, T_J = 125°C $V_R = 390V, T_J = 125^{\circ}C$ $di_F/dt = 800A/\mu s$ € MAX REVERSE RECOVERY CURRENT (A) 10 MAX REVERSE RECOVERY CURRENT 12 9 10 8 $di_F/dt = 500A/\mu s$ 7 6 6 5 $di_F/dt = 200A/\mu s$ 0 16 I_F, FORWARD CURRENT (A) di_F/dt, CURRENT RATE OF CHANGE (A/μs) Figure 5. Maximum Reverse Recovery Current Figure 6. Maximum Reverse Recovery Current vs Forward Current vs di_F/dt



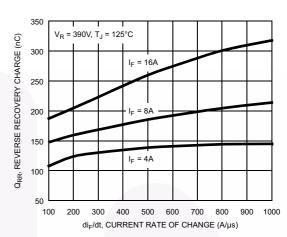


Figure 8. Reverse Recovery Charge vs di_F/dt

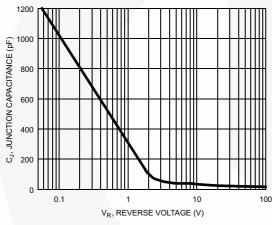


Figure 9. Junction Capacitance vs Reverse Voltage

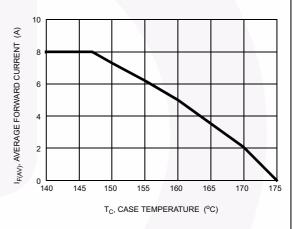


Figure 10. DC Current Derating Curve

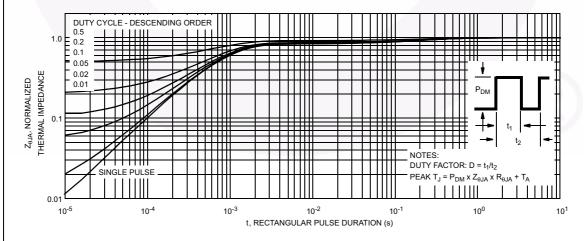
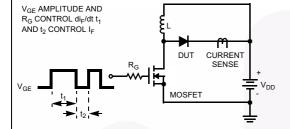


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuits and Waveforms



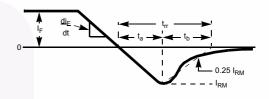
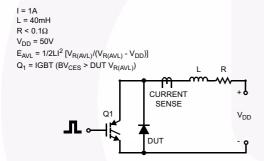


Figure 12. t_{rr} Test Circuit

Figure 13. t_{rr} Waveforms and Definitions



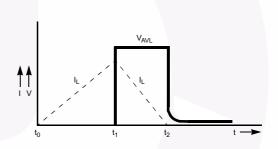


Figure 14. Avalanche Energy Test Circuit

Figure 15. Avalanche Current and Voltage Waveforms

→ 0.36M B AM 10.67 9.65 3.43 2.54 13.40 12.19 16.51 9.40 2 1.78 MAX 6.35 14.73 0.61 (1.91)2.54 ◆ 0.38M B AM 5.08 NOTES: UNLESS OTHERWISE SPECIFIED A) REFERENCE JEDEC, TO—220, ISSUE K, VARIATION AC, DATED APRIL 2002. B) ALL DIMENSIONS ARE IN MILLIMETERS. DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS. C) _ DIMENSIONING AND TOLERANCING PER ANSI Y14.5 - 1973 D)

Figure 16. TO-220 2L - 2LD,TO220,JEDEC TO-220 VARIATION AC

E)

IS OPTIONAL

PRESENCE OF TRIMMED CENTER LEAD

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN TT220-0B2.

Mechanical Dimensions

Package Dimensions 9.45 10.00 (6.40)1.78 MAX 3.80 (2.12)5.08 LAND PATTERN RECOMMENDATION UNLESS NOTED, ALL DIMS TYPICAL 5.08 → 0.25 M B AM 6.22 MIN 6.86 MIN 15.88 14.61 SEE DETA|L A NOTES: UNLESS OTHERWISE SPECIFIED A) ALL DIMENSIONS ARE IN MILLIMETERS. B) REFERENCE JEDEC, TO-263, VARIATION AB. C) DIMENSIONING AND TOLERANCING PER ANSI Y14,5M - 1994. D) LOCATION OF THE PIN HOLE MAY VARY GAGE PLANE (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE). E) LANDPATTERN RECOMMENDATION PER IPC 0.25 TO254P1524X482-3N F) FILENAME: TO263A02REV6 O.10 B 0.25 MAX (5.38)

Figure 17. TO-263 2L (D2PAK) - 2LD,TO263, SURFACE MOUNT

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

DETAIL A, ROTATED 90°

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT263-002.





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ AX-CAF BitSiC™ Build it Now™ CorePLUS™ CorePOWER™

 $CROSSVOLT^{rm}$ CTL™ Current Transfer Logic™ DEUXPEED® Dual Cool™ EcoSPARK® EfficentMax™ **ESBC™**

Fairchild[®] Fairchild Semiconductor® FACT Quiet Series™ FACT®

FAST® FastvCore™ FETBench™ FPS™

F-PFSTM FRFET®

Global Power ResourceSM GreenBridge™

Green FPS™

Green FPS™ e-Series™

 $\mathsf{G} max^\mathsf{TM}$ $\mathsf{G} \mathsf{T} \mathsf{O}^\mathsf{TM}$ IntelliMAX™ ISOPLANAR™

Marking Small Speakers Sound Louder

MegaBuck™ MICROCOUPLER™ MicroFET^T MicroPak™ MicroPak2™ MillerDrive™ MotionMax™ mWSaver[®] OptoHiT™ OPTOLOGIC®

OPTOPLANAR®

® PowerTrench® PowerXS™ Programmable Active Droop™ QFĔT®

QSTM Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™

Sync-Lock™ SYSTEM ®' **TinyBoost** TinyBuck® TinyCalc™ TinyLogic[®] TINYOPTO™ TinyPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®* μSerDes™

UHC® Ultra FRFET™ UniFET™ **VCXTM** VisualMax™ VoltagePlus™ XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their

parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 166

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

ISL9R860P2

ПОСТАВКА ЭЛЕКТРОННЫХ КОМПОНЕНТОВ

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001 Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru moschip.ru_6 moschip.ru_4 moschip.ru_9